WHAT IS CLAIMED IS:

| l | I. A method for preventing dopant leaching from a doped structural f | ilm |
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| 2 | during fabrication of a microelectromechanical system, the method comprising: | |
| 3 | producing a microstructure that includes the doped structural film, sacrific | ial |
| 4 | material, and metallic material by a combination of techniques selected from the group | |
| 5 | consisting of deposition, patterning, and etching; | |
| 6 | dissolving the sacrificial material with a release solution, the release soluti | on |
| 7 | comprising a substance destructive to the sacrificial material and acting as an electrolyte to | Ю. |
| 8 | form a galvanic cell with the doped structural film and metallic material acting as electrod | les |
| 9 | and | |
| 10 | suppressing effects of the galvanic cell by including a nonionic detergent | |
| 11 | mixed in the release solution. | |
| 1 | 2. The method recited in claim 1 wherein the release solution comprise | ses |
| 2 | an acid. | |
| | | |
| 1 | The method recited in claim 2 wherein the acid is HF. | |
| 1 | 4. The method recited in claim 1 wherein the doped structural film | |
| 2 | comprises a doped semiconductor. | |
| | | |
| 1 | 5. The method recited in claim 4 wherein the doped structural film | |
| 2 | comprises doped silicon. | |
| 1 | 6. The method recited in claim 5 wherein the doped structural film | |
| 2 | comprises doped polysilicon. | |
| | | |
| 1 | 7. The method recited in claim 1 wherein the sacrificial material | |
| 2 | comprises an oxide. | |
| 1 | 8. The method recited in claim 7 wherein the oxide is a silicon oxide. | |
| | | |
| . 1 | 9. The method recited in claim 7 wherein the oxide comprises alumin | ıa. |
| 1 | 10. The method recited in claim 1 wherein the sacrificial material | |
| 2 | comprises a nitride. | |
| | | |

The method recited in claim 10 therein the nitride is a silicon nitride. 1 1 12. The method recited in claim 7 wherein the sacrificial material 2 comprises photoresist. 1 13. The method recited in claim 1 wherein the metallic material comprises 2 gold. 1 14. The method recited in claim 1 wherein the metallic material comprises 2 aluminum. 1 The method recited in claim 1 wherein the metallic material comprises 15. 2 copper. 1 16. The method recited in claim 1 wherein the metallic material comprises 2 platinum. 1 17. The method recited in claim 1 wherein the metallic material comprises 2 nickel 1 18. The method recited in claim 1 wherein the nonionic detergent 2 comprises an alkyl group and a polyether-linked hydroxy group commonly linked to an aryl 3 group. The method recited in claim 18 wherein the nonionic detergent 1 19. 2 comprises a Triton X[™] detergent. 1 20. The method recited in claim 18 wherein the nonionic detergent 2 comprises Triton X-100.™ 1 21. The method recited in claim 20 wherein the Triton X-100™ is included 2 in the release solution with a concentration approximately between 0.01 and 0.1 vol. %. 1 22. The method recited in claim 1 wherein the nonionic detergent 2 comprises Igepal CA-630.™ 1 23. The method recited in claim 1 wherein the nonionic detergent

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comprises Nonidet P-40.™

| I | 24. The method recited in claim I wherein the nonionic detergent |
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| 2 | comprises a hydrophilic moiety and a hydrophobic moiety commonly linked to an aryl group. |
| 1 | 25. The method recited in claim I wherein the microelectromechanical |
| 2 | system is surface micromachined. |
| 1 | 26. The method recited in claim 1 wherein the microelectromechanical |
| 2 | system comprises part of a mirror array for use in a wavelength router. |
| 1 | 27. A microelectromechanical system made according to the method |
| 2 | recited in claim 1. |
| 1 | 28. A method for preventing dopant leaching from a doped polysilicon |
| 2 | structural film during fabrication of a surface micromachined mirror array having a plurality |
| 3 | of moveable reflective surfaces for use in a wavelength router, the method comprising: |
| 4 | producing a mirror microstructure that includes the doped polysilicon, |
| 5 | sacrificial silicon oxide material, and gold by a combination of techniques selected from the |
| 6 | group consisting of deposition, patterning, and etching; |
| 7 | dissolving the silicon oxide material with a release solution, the release |
| 8 | solution comprising HF and acting as an electrolyte forming a galvanic cell with the doped |
| 9 | polysilicon structural film and gold acting as electrodes; and |
| 10 | suppressing effects of the galvanic cell by including a nonionic detergent |
| 11 | mixed in the release solution. |
| | |
| 1 | 29. The method recited in claim 28 wherein the nonionic detergent |
| 2 | comprises an alkyl group and a polyether-linked hydroxy group commonly linked to an aryl |
| 3 | group. |
| 1 | 30. The method recited in claim 29 wherein the nonionic detergent |
| 2 | comprises a Triton X [™] detergent. |
| 1 | 31. The method recited in claim 29 wherein the nonionic detergent |
| 2 | comprises Triton X-100.™ |
| 1 | 32. The method recited in claim 28 wherein the nonionic detergent |
| 2 | comprises a hydrophilic moiety and a hydrophobic moiety commonly linked to an aryl group. |

| 1 | 33. A surface micromachined mirror array made according to the method |
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| 2 | recited in claim 28. |
| 1 | 34. A method for fabricating a routing mechanism for use in a wavelength |
| 2 | router of the type configured to receive, at an input port, light having a plurality of spectral |
| 3 | bands and to direct subsets of the spectral bands to respective ones of a plurality of output |
| 4 | ports by providing optical paths in a free-space optical train disposed between the input ports |
| 5 | and the output ports and by providing the routing mechanism to direct a given spectral band |
| 6 | to different output ports depending on a state of a dynamically configurable routing unit in |
| 7 | the routing mechanism, the method comprising: |
| 8 | forming a plurality of such dynamically configurable routing units on a doped |
| 9 | structural film with sacrificial material and metallic material by a combination of techniques |
| .0 | selected from the group consisting of deposition, patterning, and etching; |
| . 1 | dissolving the sacrificial material with a release solution, the release solution |
| .2 | comprising a substance destructive to the sacrificial material and acting as an electrolyte |
| . 3 | forming a galvanic cell with the doped structural film and metallic material acting as |
| 4 | electrodes; and |
| .5 | suppressing the effects of the galvanic cell by including a nonionic detergent |
| 16 | mixed in the release solution, |
| 17 | whereby dopant leaching from the doped structural film due to the effects of |
| 8 | the galvanic cell is suppressed. |
| 1 | 35. The method recited in claim 34 wherein the nonionic detergent |
| 2 | comprises an alkyl group and a polyether-linked hydroxy group commonly linked to an aryl |
| 3 | group. |
| 1 | 36. The method recited in claim 35 wherein the nonionic detergent |
| 2 | comprises a Triton X [™] detergent. |
| 1 | 37. The method recited in claim 35 wherein the nonionic detergent |
| 2 | comprises Triton X-100 TM |
| | |

comprises a hydrophilic moiety and a hydrophobic moiety commonly linked to an aryl group.

The method recited in claim 34 wherein the nonionic detergent

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- 1 39. The method recited in claim 34 wherein the release solution comprises
- 2 HF, the doped structural film comprises doped polysilicon, the sacrificial material comprises
- 3 a silicon oxide, the metallic material comprises gold, and the nonionic detergent comprises
- 4 Triton X-100.™
- 1 40. A routing mechanism made according to the method recited in claim
- 2 39.
- 1 41. A routing mechanism made according to the method recited in claim
- 2 34.
- 1 42. A wavelength router comprising a routing mechanism made according
- 2 to the method recited in claim 34.